DESCRIPTION

SP6037 is a high performance and tightly integrated secondary side synchronous rectifying converter for switching mode power supply system. It combines a low Rdson N-channel MOSFET to emulate the traditional diode rectifier at the secondary side of Flyback converter, The fundamental of SP6037 synchronous rectifying (SR) converter is based on our U.S. patented methods that utilize the principle of "prediction" logic circuit. The IC deliberates previous cycle timing to control the SR in present cycle by "predictive" algorithm that makes adjustments to the turn-off time, in order to achieve maximum efficiency and avoid crossconduction at the same time. The SP6037 is capable to adapt in almost all existing 5V Resonance converters with few adjustments considered necessary.

FEATURES

- Offers efficiency improvement over Schottky Diode.
- Low Standby Power to meet DOE Lot 6 requirement.
- Secondary-side synchronous rectifier optimized for 5V output system.
- Build-in 45V SR MOSFET with low Rdson
- Operating frequency up to 300 KHz.
- Synchronize to transformer primary voltage waveform.
- Internal over voltage protection

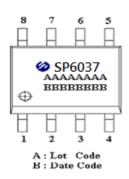
APPLICATIONS

- Switching Mode Power Supply (CCM&DCM&QR)
- Storage area network power supplies
- Telecommunication converters
- Embedded systems
- Industrial & commercial systems using high current processors
- Power converters to meet Lot 6 requirement

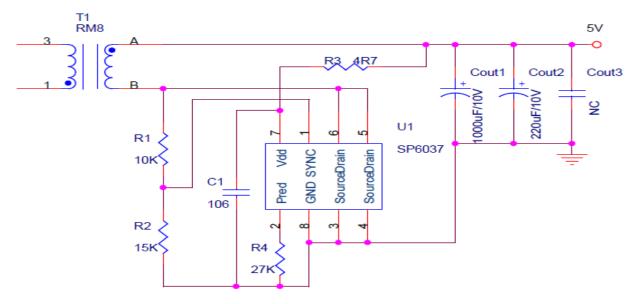
PIN CONFIGURATION (SOP-8)



PART MARKING



TYPICAL APPLCATION CIRCUIT



PIN DESCRIPTION

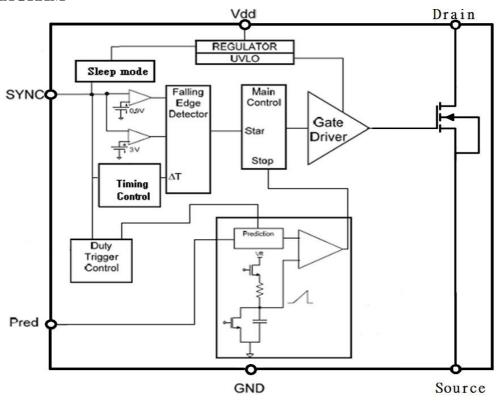
PinSymbolDescription1SYNCSynchronized signal from Vds of SR MOSFET2PredBy connecting a resistor to ground to set the dead time.3SourceInternal MOSFET Source4SourceInternal MOSFET Source5DrainInternal MOSFET drain6DrainInternal MOSFET drain7VddDC supply voltage.8GNDGround connection.		KII IION	
Pred By connecting a resistor to ground to set the dead time. Source Internal MOSFET Source Internal MOSFET Source Drain Internal MOSFET drain Drain Internal MOSFET drain Vdd DC supply voltage.	Pin	Symbol	Description
3 Source Internal MOSFET Source 4 Source Internal MOSFET Source 5 Drain Internal MOSFET drain 6 Drain Internal MOSFET drain 7 Vdd DC supply voltage.	1	SYNC	Synchronized signal from Vds of SR MOSFET
4 Source Internal MOSFET Source 5 Drain Internal MOSFET drain 6 Drain Internal MOSFET drain 7 Vdd DC supply voltage.	2	Pred	By connecting a resistor to ground to set the dead time.
5 Drain Internal MOSFET drain 6 Drain Internal MOSFET drain 7 Vdd DC supply voltage.	3	Source	Internal MOSFET Source
6 Drain Internal MOSFET drain 7 Vdd DC supply voltage.	4	Source	Internal MOSFET Source
7 Vdd DC supply voltage.	5	Drain	Internal MOSFET drain
	6	Drain	Internal MOSFET drain
8 GND Ground connection.	7	Vdd	DC supply voltage.
	8	GND	Ground connection.

ORDERING INFORMATION

Part Number	Package	Part Marking
SP6037S8RGB	SOP-8	SP6037

※ SP6037S8RGB: Tape Reel; Pb − Free; Halogen - Free

BLOCK DIAGRAM



ABSOULTE MAXIMUM RATINGS (TA=25°C, unless otherwise specified.)

The following ratings designate persistent limits beyond which damage to the device may occur.

Symbol	Parameter	Value	Unit	
V_{dd}	DC Supply Voltage	16	V	
Vd to Vs	Drain to Source	45	V	
P_D	Power Dissipation @ $T_A=25^{\circ}C$ (*)	3.1	W	
T_{J}	Operating Junction Temperature Range	-40 to125	$^{\circ}\!\mathbb{C}$	
T_{STG}	Storage Temperature Range	-40 to 150	$^{\circ}\mathbb{C}$	
T_{LEAD}	Lead Soldering Temperature for 5 sec.	260	$^{\circ}\mathbb{C}$	

THERMAL RESISTANCE

Symbol	Parameter	Valu	Unit
Rөja	Thermal Resistance-Junction to Ambient (*)	110	°C/W

^(*) The power dissipation and thermal resistance are evaluated under copper board mounted with free air conditions.



ELECTRICAL CHARACTERISTICS

(T_A=25 $^{\circ}\text{C}$, V_dd=5V, Freq. =50 KHz, Duty Cycle=50%, unless otherwise specified.)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
SUPPLY IN	PUT					
Idd	Supply current	No load & Sleep mode V _{SYNC} =Vdd ,No load	2.0	0.2 3.0	0.35 4.0	mA mA
Vdd	Supply voltage	Idd peak < 1A	4.5		16	V
Vovp	Over voltage protection		17	17.8	18.5	V
Vdd on	Enable voltage		3.4	3.7	4.1	V
Vdd hysteresis	Enable voltage		0.1	0.3	0.5	V
SYNC REFE	CRENCE (SYNC)					
Vshth	SYNC high threshold			3.0		V
Vslth	SYNC low threshold			0.9		V
Vsync	SYNC clamp voltage	Isync=3mA	Vdd+1.5			V
Vsync WK	SYNC wake-up voltage	Pulse width >1uS for Vdd=5V	6			V
Isync	SYNC input current				3	mA
PREDICTIO	ON SECTION					•
Vpred		Pin1=15KΩ		1.25		V
Td	Propagation delay	Pin1=15KΩ		120		
Tpred	Dead time	Pin1=15KΩ		450		
Tr	Rise time	Load=1nF		11		nS
Tf	Fall time	Load=1nF		8		
SR MOSFET	SECTION	•	•			•
BVdss	Drain-Source Breakdown Voltage	$V_{GS}=0V,I_D=250uA$	45			V
E _{AS}	Avalanche Energy with Single Pulse	$T_C=25^{\circ}C$, L=0.4mH.		20		mJ
R _{DS(on)}	Drain-Source On-Resistance	$V_{GS} = 4.5V, I_D = 8A$		10	14	mΩ
Ciss	Input Capacitance			942		
Coss	Output Capacitance	$V_{DS}=20V, V_{GS}=0V, f=1MHz$		309		pF
Crss	Reverse Transfer Capacitance]		29] ^
Td(on)	Turn On Time	V_{DS} =20V, I_{D} =10A, V_{GS} =10V,		6		nS
Td(off)	Turn Off Time	$Rg=10\Omega$		21		113

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